



2SA1257/2SC3143

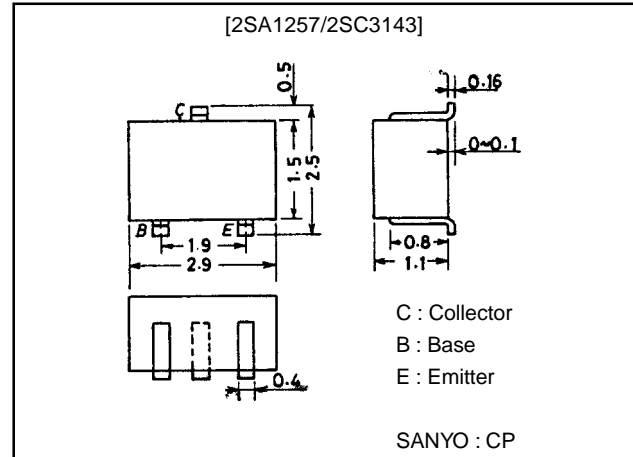
High-Voltage Switching, AF Power Amp, 100W Output Predriver Applications

Features

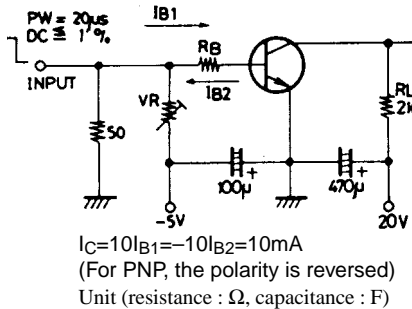
- Very small-sized package permitting the 2SA1257/2SC3143-applied sets to be made small and slim.
- High breakdown voltage ($V_{CEO} \geq 160V$).
- Small output capacitance.

Package Dimensions

unit:mm
2018A



Switching Time Test Circuit



() : 2SA1257

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)180	V
Collector-to-Emitter Voltage	V_{CEO}		(-)160	V
Emitter-to-Base Voltage	V_{EBO}		(-)5	V
Collector Current	I_C		(-)80	mA
Collector Current Pulse	I_{CP}		(-)150	mA
Collector Dissipation	P_C		200	mW
Junction Temperature	T_j		125	$^\circ C$
Storage Temperature	T_{stg}		-55 to +125	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)120V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = (-)5V, I_C = (-)10mA$	60*		270*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10V, I_C = (-)10mA$		(130) 150		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-)10V, f = 1MHz$		(2.4) 2.0	(3.2) 2.8	pF
Base-to-Emitter Voltage	V_{BE}	$V_{CE} = (-)5V, I_C = (-)10mA$			(-)1.5	V
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)30mA, I_B = (-)3mA$			(-)0.7	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)180			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)160			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V
Turn-ON Time	t_{on}	See specified Test Circuit		(0.15) 0.18		μs
Storage Time	t_{stg}	See specified Test Circuit		(0.95) 1.00		μs
Fall Time	t_f	See specified Test Circuit		(0.15) 0.20		μs

* : The 2SA1257/2SC3143 are classified by 10mA h_{FE} as follows :

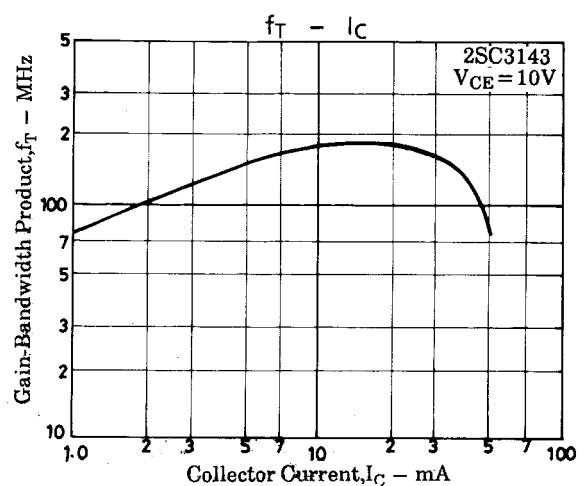
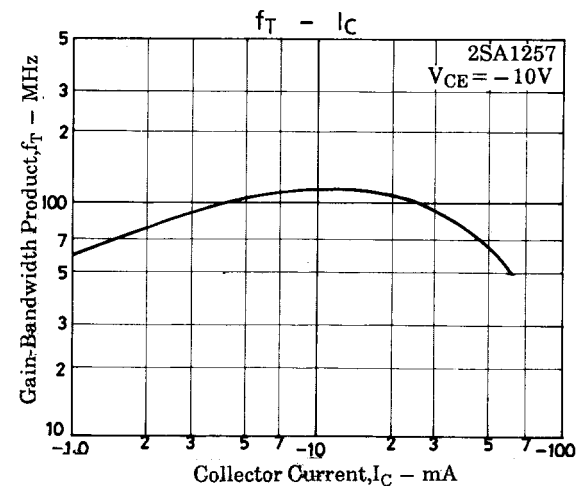
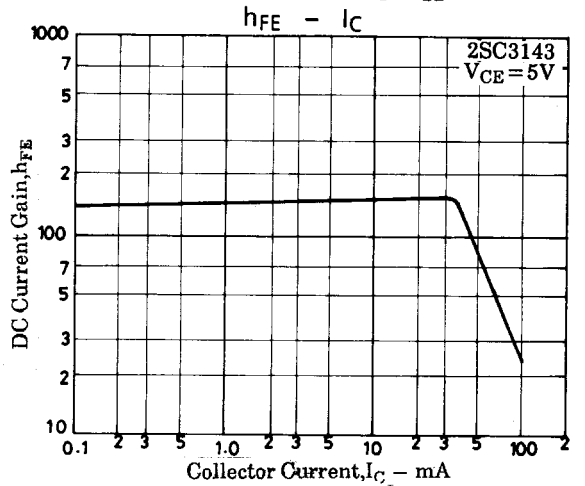
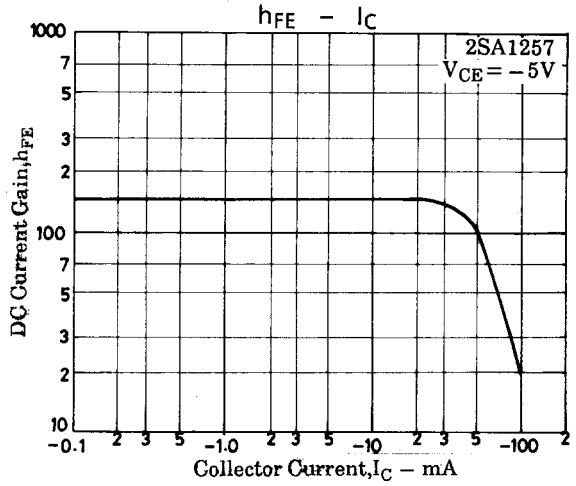
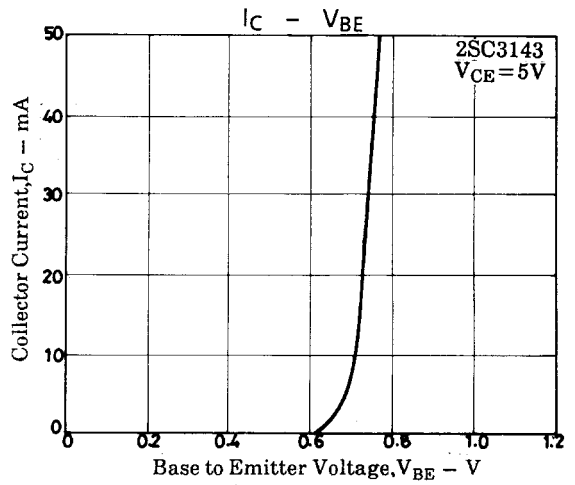
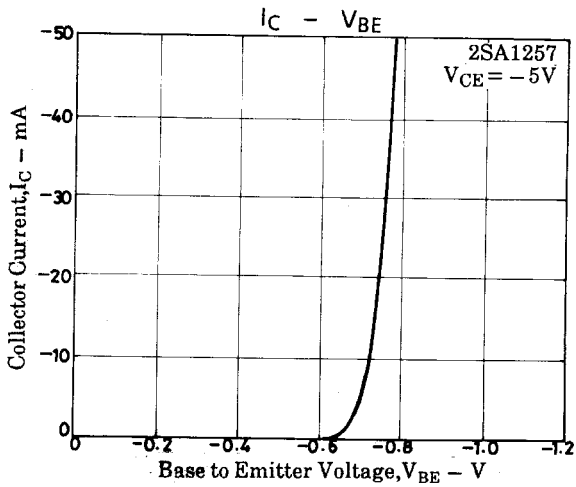
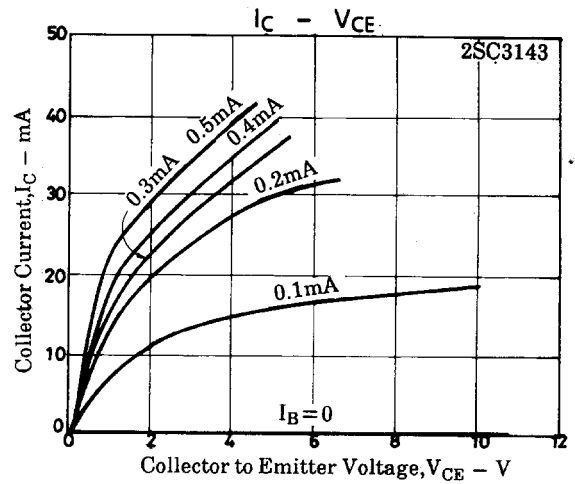
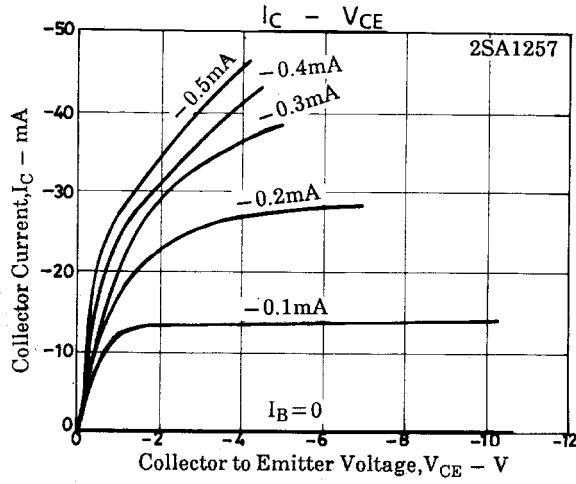
60	G3	120	90	G4	180	135	G5	270
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Marking 2SA1257 : G, 2SC3143 : K, h_{FE} rank : 3, 4, 5

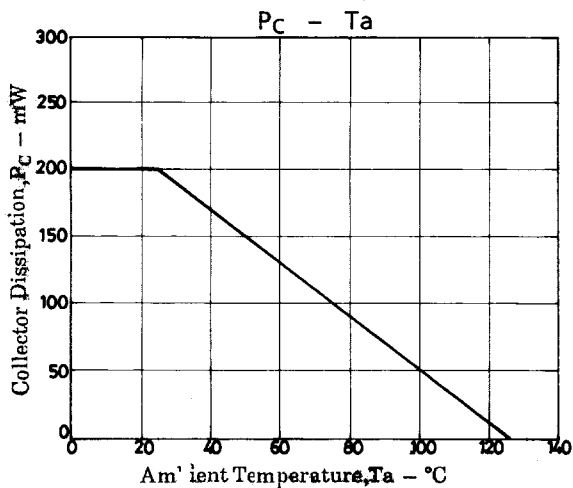
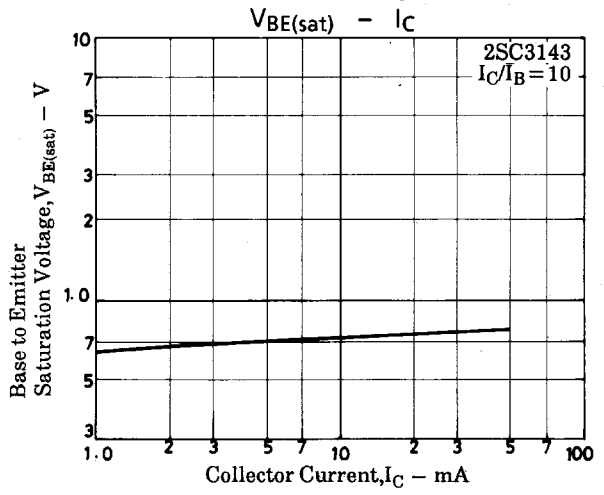
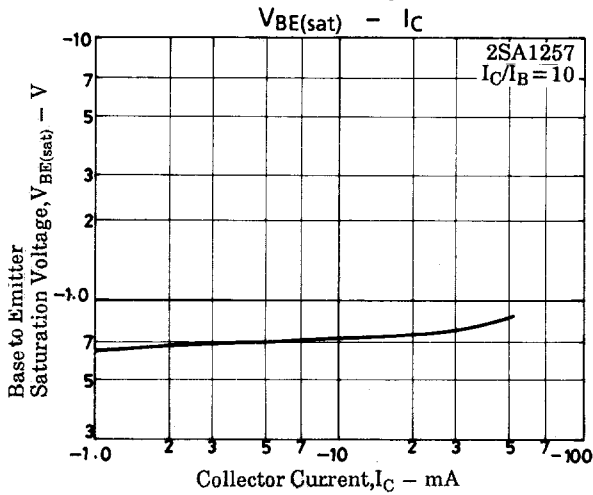
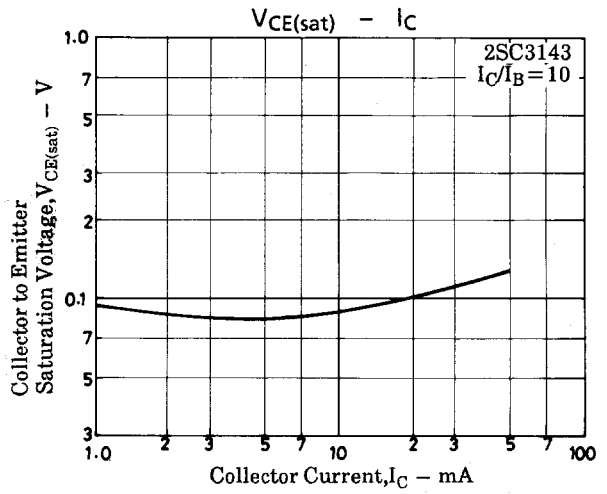
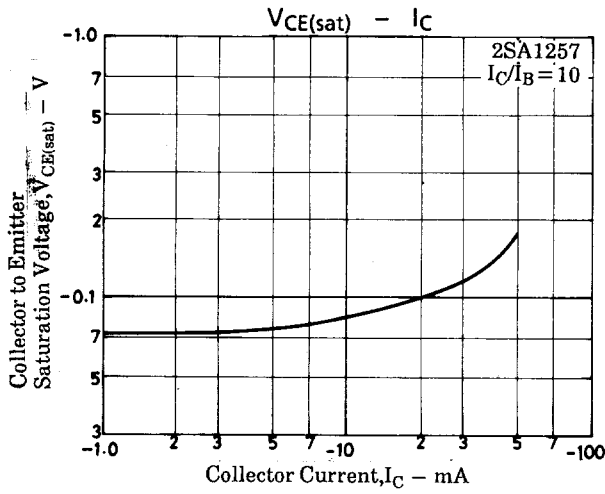
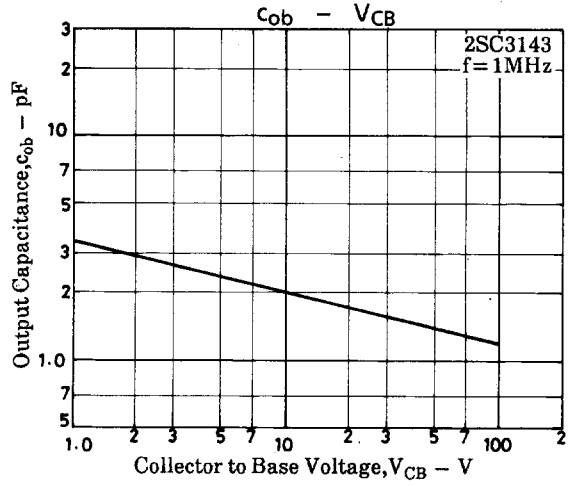
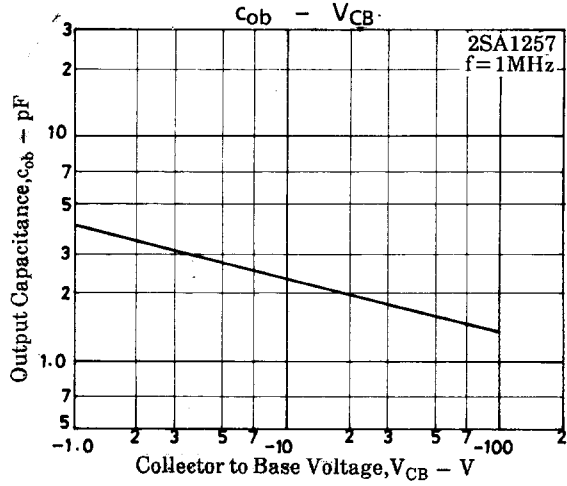
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